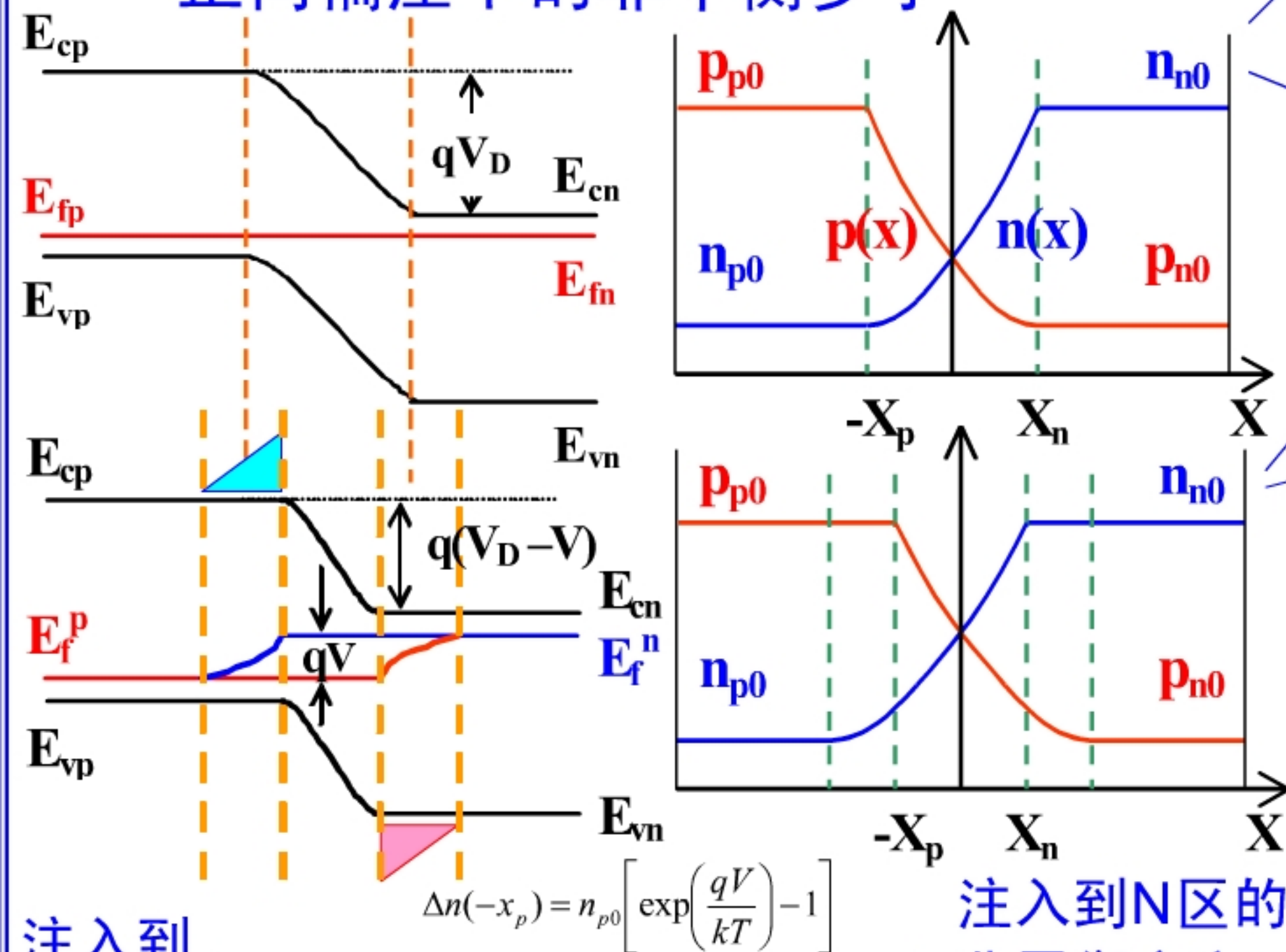


# 8.2 p-n结电流电压特性8

## 8.2.2 非平衡p-n结的能带图

— 正向偏压下的非平衡少子



$$n(-x_p) = n_{p0} = n_{n0} \exp\left(-\frac{qV_D}{kT}\right)$$

$$p(x_n) = p_{n0} = p_{p0} \exp\left(-\frac{qV_D}{kT}\right)$$

$$p(x_n) = p_{p0} \exp\left(-\frac{q(V_D - V)}{kT}\right)$$

$$p(x_n) = p_{n0} \exp\left(\frac{qV}{kT}\right)$$

$$\Delta p(x_n) = p_{n0} \left[ \exp\left(\frac{qV}{kT}\right) - 1 \right]$$

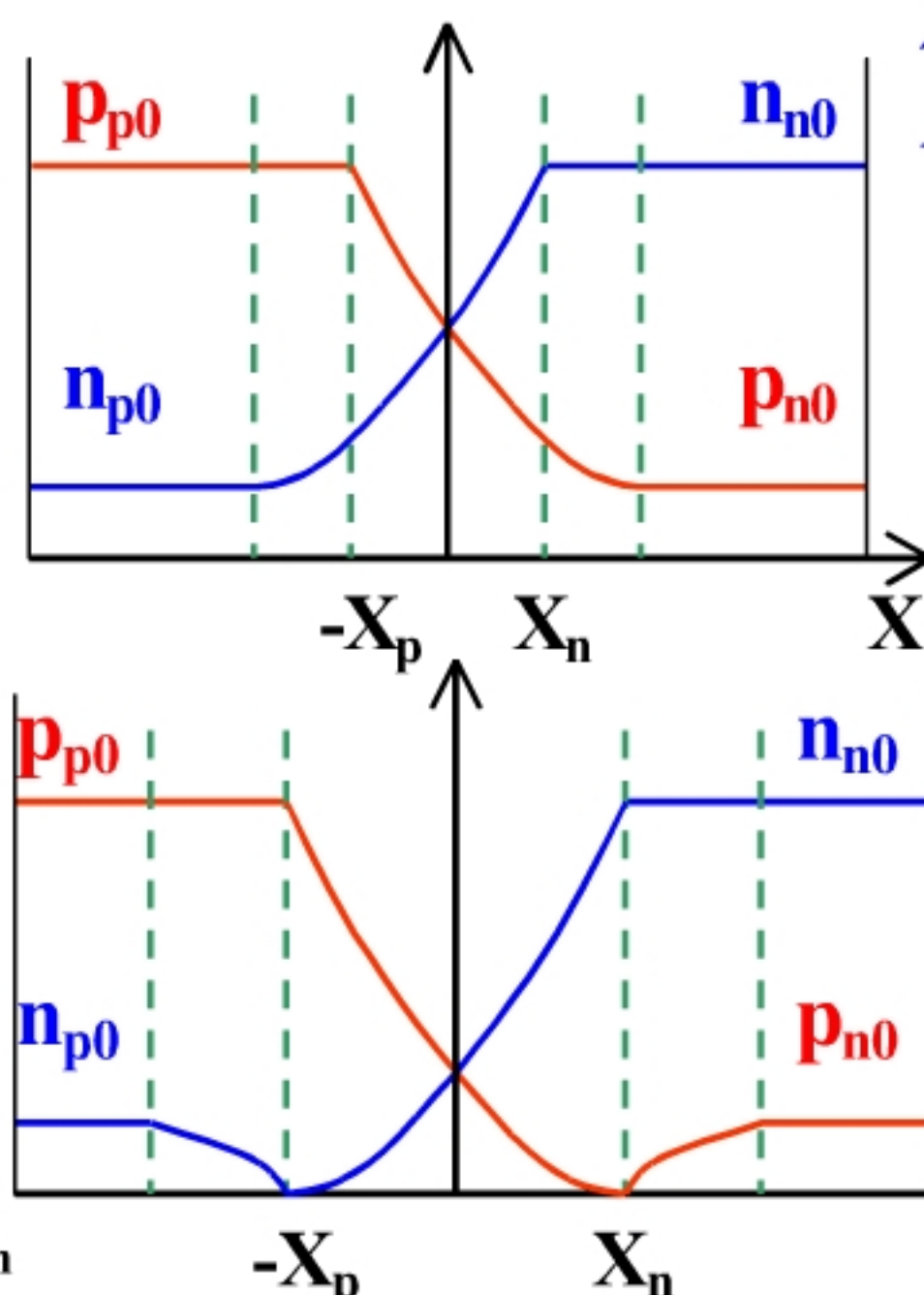
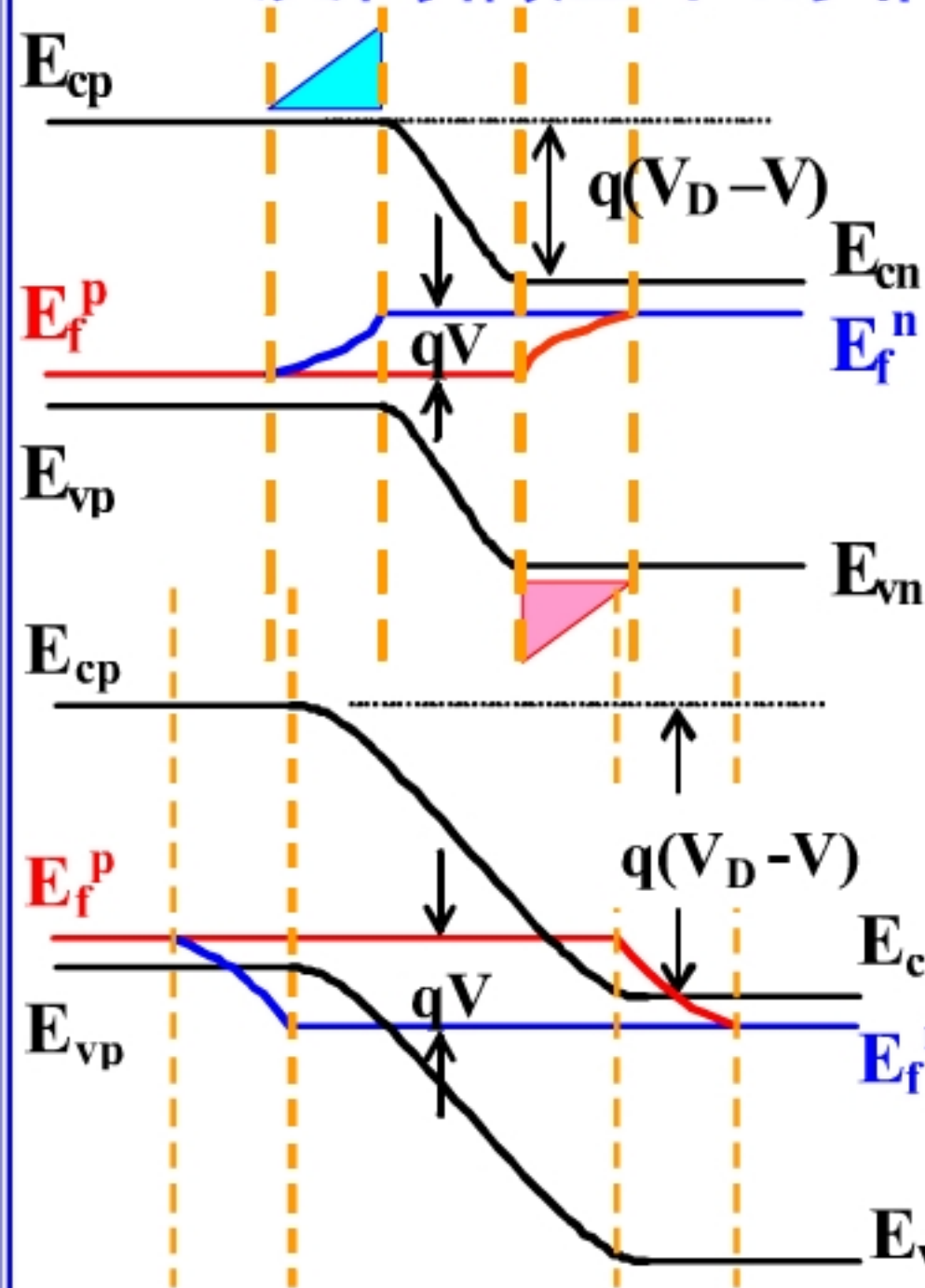
$$x > x_n \quad \Delta p(x) = p(x) - p_{n0}$$

$$\Delta p(x) = \Delta p(x_n) \exp\left(-\frac{x - x_n}{L_p}\right)$$

# 8.2 p-n结电流电压特性<sub>9</sub>

## 8.2.2 非平衡p-n结的能带图

—反向偏压下的非平衡少子



$$\Delta p(x_n) = p_{n0} \left[ \exp\left(\frac{qV}{kT}\right) - 1 \right]$$

$$\Delta n(-x_p) = n_{p0} \left[ \exp\left(\frac{qV}{kT}\right) - 1 \right]$$

$$\Delta p(x) = \Delta p(x_n) \exp\left(-\frac{x - x_n}{L_p}\right)$$

$$\Delta n(x) = \Delta n(-x_p) \exp\left(\frac{x + x_p}{L_n}\right)$$

$$V < 0 \quad q|V| \gg kT \quad = 0$$

抽取

$$\Delta p(x_n) = p(x_n) - p_{n0} = -p_{n0}$$

$$\Delta n(-x_p) = n(-x_p) - n_{p0} = -n_{p0}$$

$$\Delta n(x) = -n_{p0} \exp\left(\frac{x + x_p}{L_n}\right)$$

$$\Delta p(x) = -p_{n0} \exp\left(-\frac{x - x_n}{L_p}\right)$$



# 8.2 p-n结电流电压特性<sup>10</sup>

## 8.2.3 理想p-n结的J-V关系

前提:

- 小注入  $\Delta n_p \ll p_{p0}$   $\Delta p_n \ll n_{n0}$
- 突变耗尽层条件 (耗尽层外电中性)
- 忽略势垒区中载流子的产生、复合
- 非简并

**电流密度**

$$J = J_p(x_n) + J_n(x_n)$$

扩散电流组成

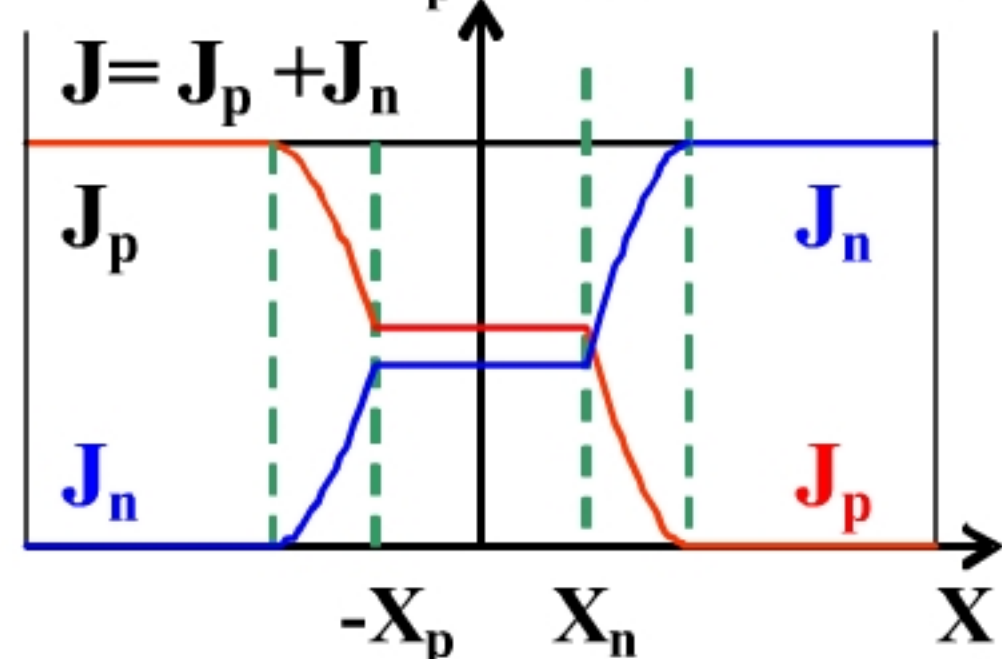
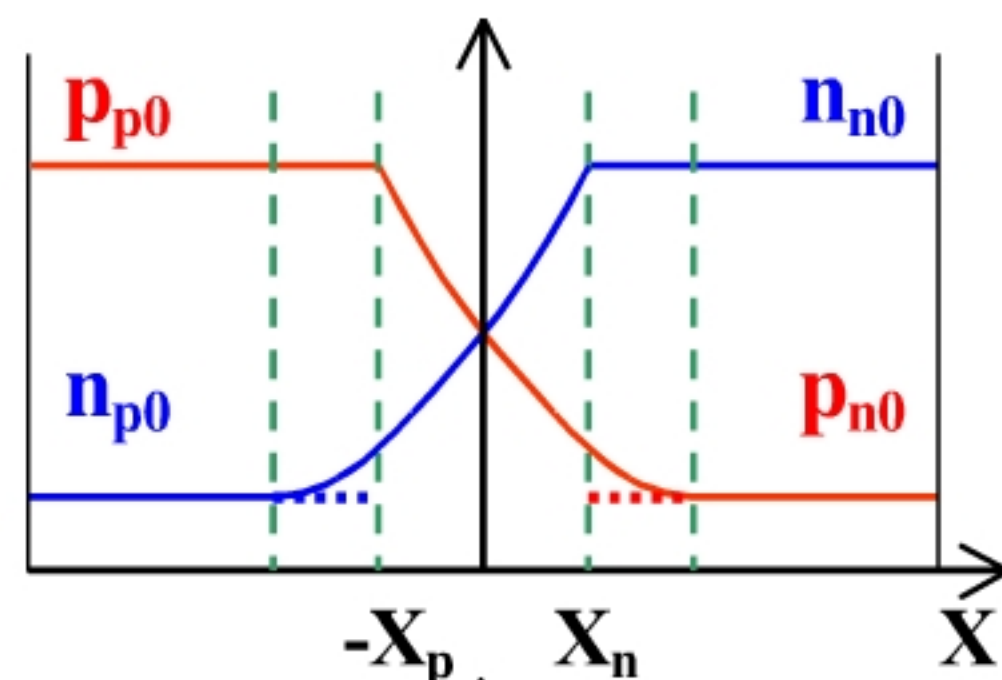
$$J = J_p + J_n = J_p(x_n) + J_n(-x_p)$$

$$\Delta p(x) = \Delta p(x_n) \exp\left(-\frac{x-x_n}{L_p}\right) \leftarrow \Delta p(x_n) = p_{n0} \left[ \exp\left(\frac{qV}{kT}\right) - 1 \right]$$

$$J_p(x_n) = -qD_p \frac{d\Delta p}{dx} \Big|_{x=x_n} = \frac{qD_p}{L_p} p_{n0} \left[ \exp\left(\frac{qV}{kT}\right) - 1 \right] \leftrightarrow J_n(-x_p) = \frac{qD_n}{L_n} n_{p0} \left[ \exp\left(\frac{qV}{kT}\right) - 1 \right]$$

$$J_s = \left( \frac{qD_p n_i^2}{L_p N_D} + \frac{qD_n n_i^2}{L_n N_A} \right) \quad p_{n0} = \frac{n_i^2}{N_D} \quad n_{p0} = \frac{n_i^2}{N_A}$$

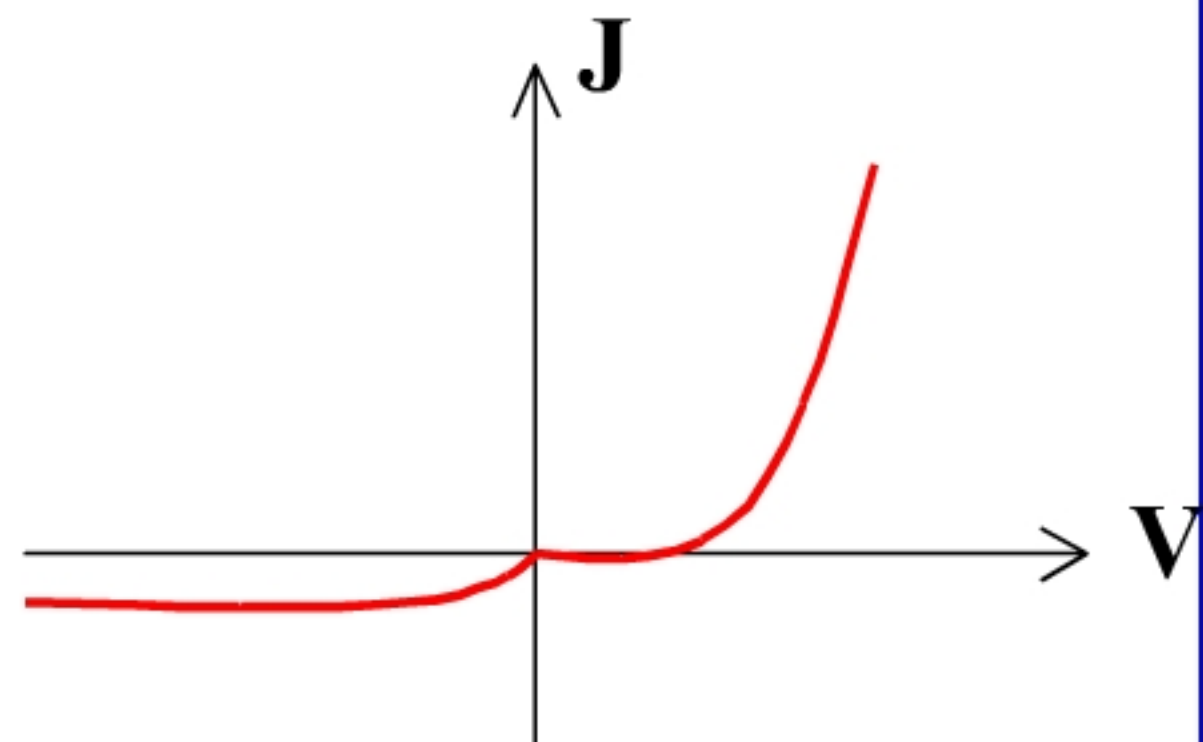
$$J = J_s \left[ \exp\left(\frac{qV}{kT}\right) - 1 \right]$$



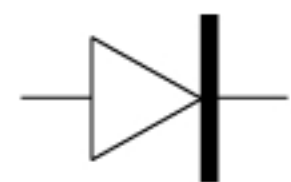
## 8.2 p-n结电流电压特性<sub>11</sub>

### 8.2.4 理想p-n结J-V关系的特性

$$J = J_s \left[ \exp\left(\frac{qV}{kT}\right) - 1 \right] \quad J_s = \left( \frac{qD_p n_i^2}{L_p N_D} + \frac{qD_n n_i^2}{L_n N_A} \right)$$



—整流特性



$$J = J_s \exp\left(\frac{qV}{kT}\right) \quad qV/kT \gg 1$$
$$J = -J_s \quad -qV/kT \gg 1$$

$J_s$ : 反向饱和电流密度

—强烈依赖温度

$$J_s \propto T^{3+\frac{\gamma}{2}} \exp\left(-\frac{E_g}{kT}\right)$$

$$J \propto T^{3+\frac{\gamma}{2}} \exp\left[\frac{q(V - V_{g0})}{kT}\right]$$

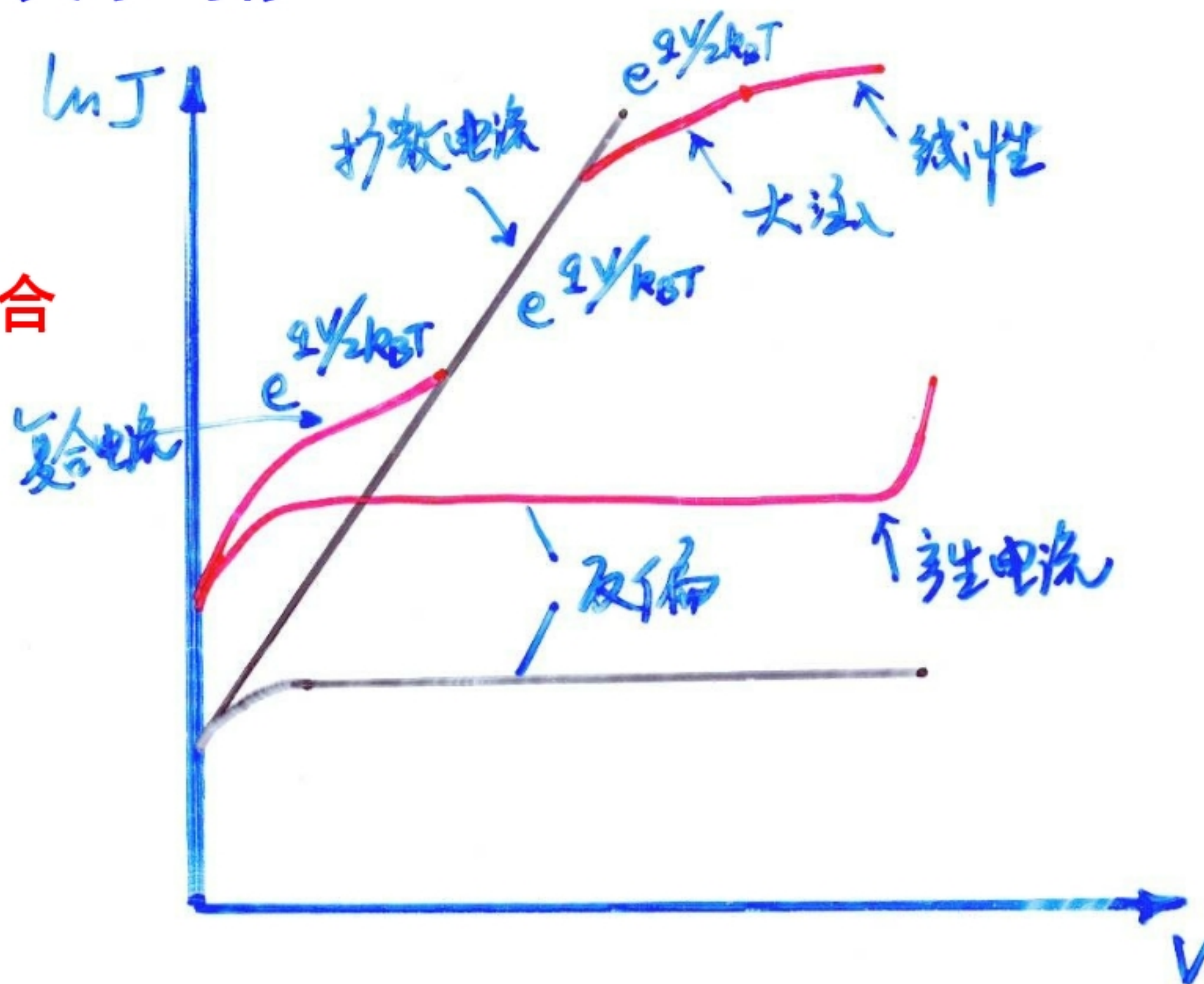


## 8.2 p-n结电流电压特性<sup>12</sup>

### 8.2.5 理想p-n结J-V关系的修正

可能因素:

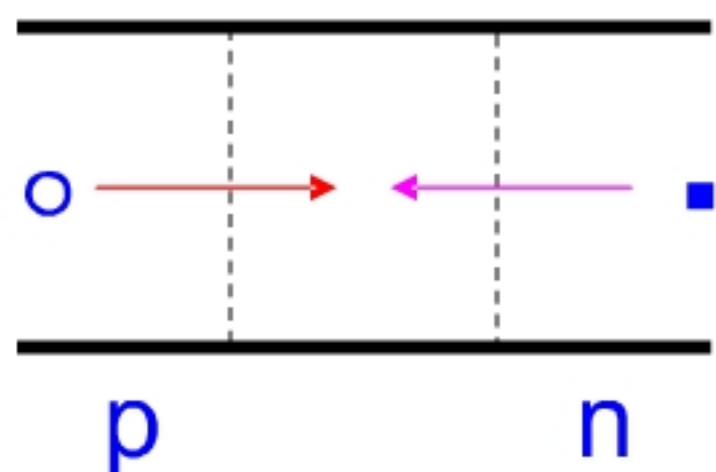
- 表面效应
- 势垒区中的产生和复合
- 大注入条件
- 串联电阻



## 8.2 p-n结电流电压特性<sub>13</sub>

### 8.2.5 理想p-n结J-V关系的修正

—复合电流(正向偏压)



假设  $E_t = E_i$ ,  $n_1 = p_1 = n_i$ ,  $r_n = r_p = r$

$$U = \frac{N_t r_n r_p (np - n_i^2)}{r_n (n + n_1) + r_p (p + p_1)} = \frac{N_t r (np - n_i^2)}{n + p + 2n_i}$$

$$\left. \begin{aligned} n &= n_i \exp\left(\frac{E_F^n - E_i}{kT}\right) \\ p &= n_i \exp\left(\frac{E_i - E_F^p}{kT}\right) \end{aligned} \right\} \Rightarrow np = n_i^2 \exp\left(\frac{E_F^n - E_F^p}{kT}\right) = n_i^2 \exp(qV_f / kT)$$

$n = p$  时

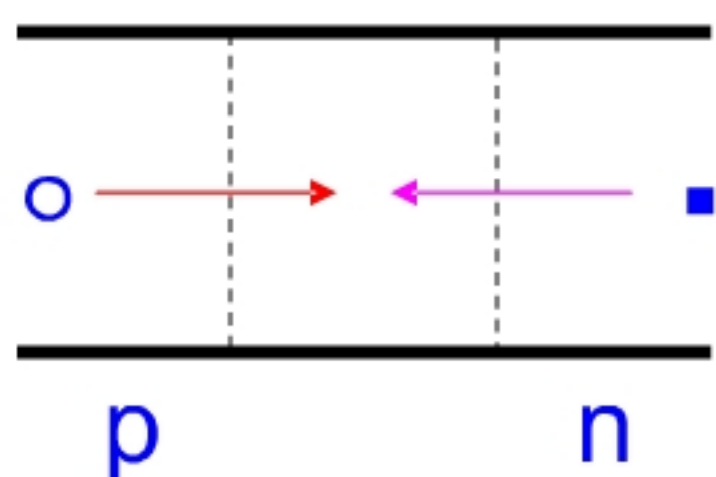
$$U_{\max} = \frac{1}{2} \frac{n_i}{\tau} \exp(qV_f / 2kT) \quad (qV_f \gg kT)$$



# 8.2 p-n结电流电压特性<sub>14</sub>

## 8.2.5 理想p-n结J-V关系的修正

—复合电流(正向偏压)

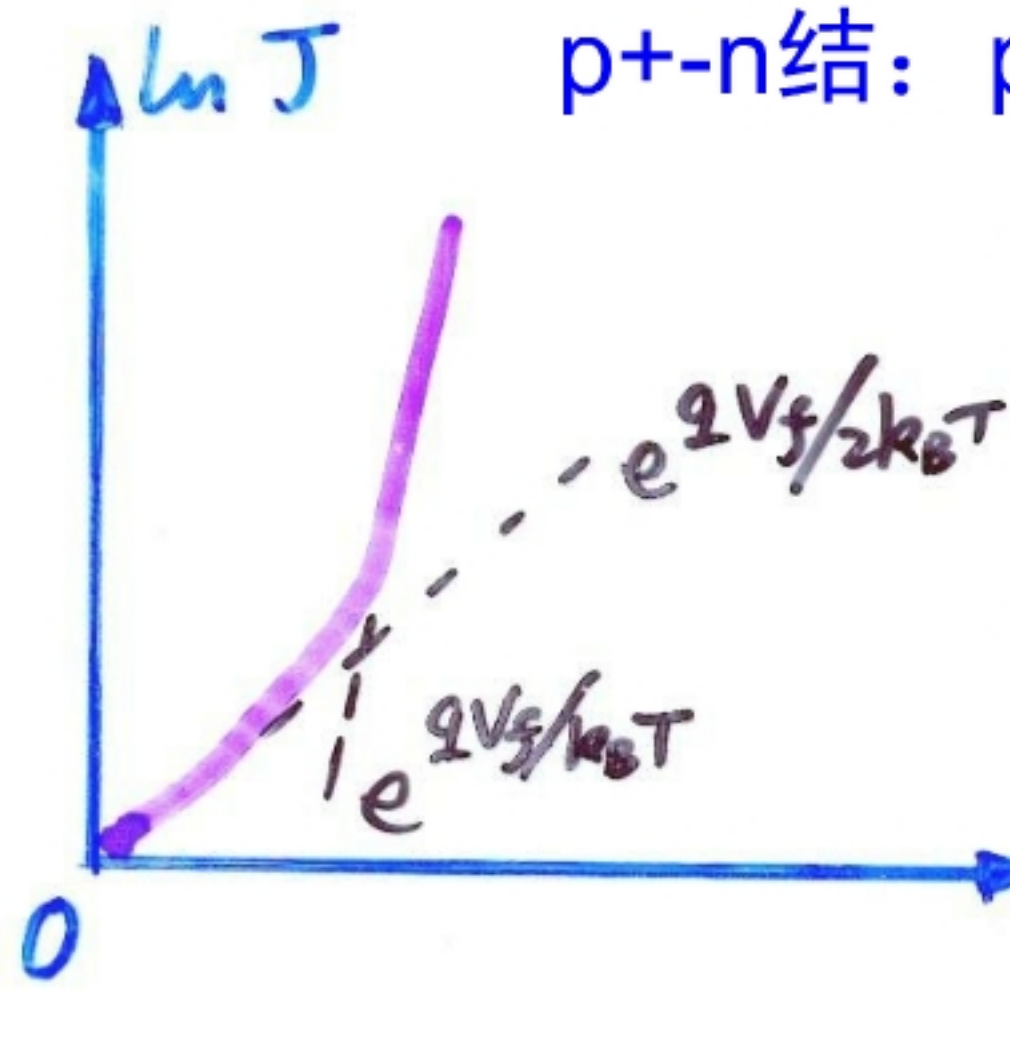


$$U_{\max} = \frac{1}{2} \frac{n_i}{\tau} \exp(qV_f / 2kT) \quad (qV_f \gg kT)$$

$$J_r = \int_{-x_p}^{x_n} qU_{\max} dx = qU_{\max} X_D = \frac{qn_i X_D}{2\tau} \exp(qV_f / 2kT)$$

p+-n结:  $p_{n0} \gg n_{p0}$  &  $qV \gg kT$

$$J_{fd} = \frac{qD_p n_i^2}{L_p N_D} \exp\left(\frac{qV}{kT}\right)$$



$$\frac{J_{fd}}{J_r} \propto \frac{2n_i L_p}{N_D X_D} \exp(qV / 2kT)$$

$$\begin{aligned} J_r &> J_{fd} \quad (V \ll 1) \\ J_{fd} &> J_r \quad (V \gg 1) \end{aligned}$$

J-V经验公式

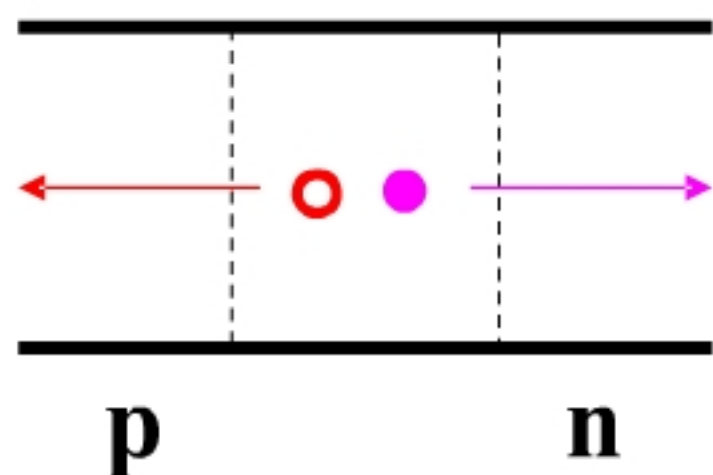
$$J_f \propto \exp(qV_f / mkT)$$

理想因子  $m: 1 \sim 2$

## 8.2 p-n结电流电压特性<sup>15</sup>

### 8.2.5 理想p-n结J-V关系的修正

—产生电流(反向偏压)



$$n_i \gg n, p; E_t = E_i; r_n = r_p = r$$

$$U = \frac{N_t r_n r_p (np - n_i^2)}{r_n (n + n_1) + r_p (p + p_1)} = -\frac{n_i}{2\tau}$$

$$J_G = qGX_D = q\frac{n_i}{2\tau}X_D \quad G = -U = \frac{n_i}{2\tau}$$

$$\frac{J_{rd}}{J_G} = 2\frac{n_i}{N_D}\frac{L_p}{X_D}$$

p+-n结

$$J_{rd} = J_s = \frac{qD_p n_i^2}{L_p N_D}$$

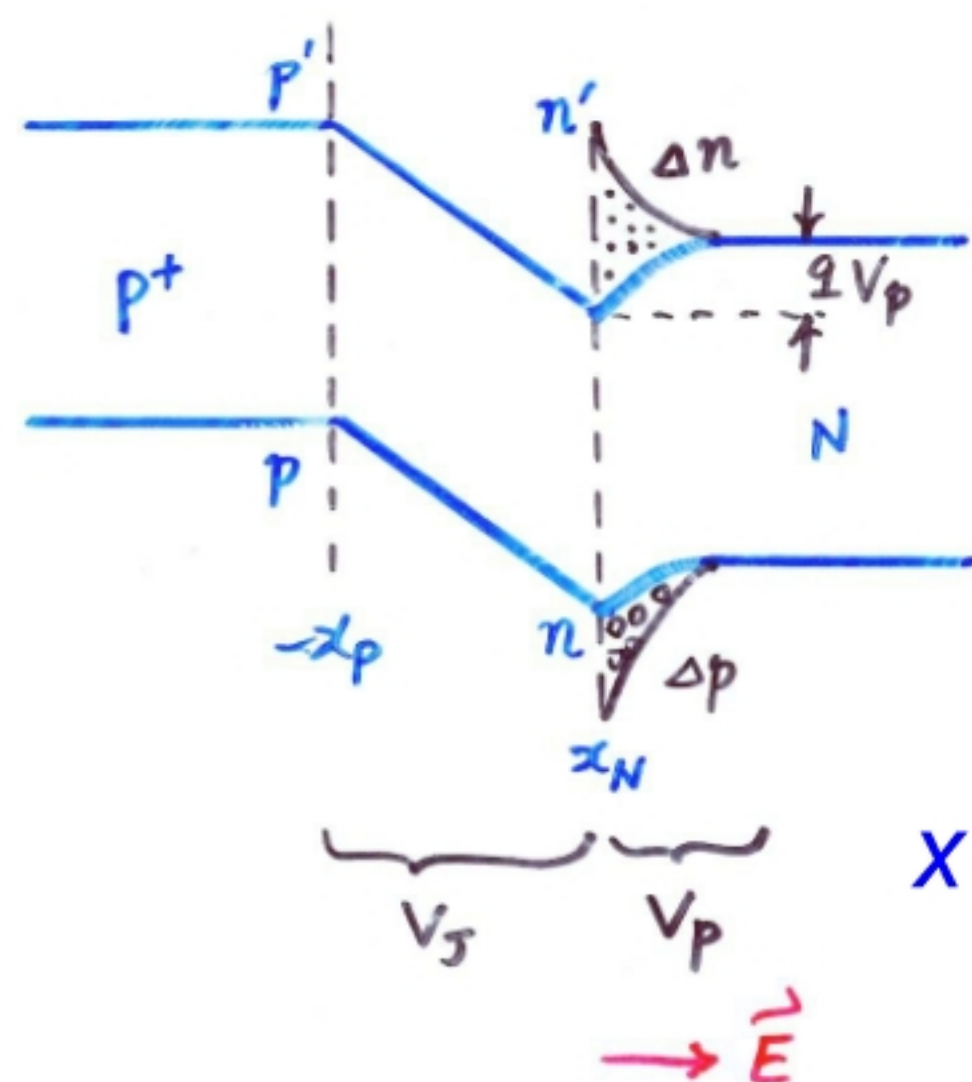
- $J_s$ 与反向偏压无关, $J_G$ 随反向偏压增加而增加
- 禁带宽度小的半导体,反向漏电流将明显增加
- 温度升高,反向漏电流将增加
- 少子寿命越小,反向漏电流也就越大



# 8.2 p-n结电流电压特性<sub>16</sub>

## 8.2.5 理想p-n结J-V关系的修正

—大注入条件(正向大偏压)



p<sup>+</sup>n 结  $\Delta p_n(x_n) \geq n_{n0} = N_D$

电中性条件  $\Delta p_n(x) = \Delta n_n(x)$   

$$\frac{d\Delta p_n(x)}{dx} = \frac{d\Delta n_n(x)}{dx}$$

内建电场  $J_n = 0$   $V = V_J + V_P$

$x = x_n$   $J_p = q\mu_p p_n(x_n)E(x_n) - qD_p \left. \frac{d\Delta p_n(x)}{dx} \right|_{x=x_n}$

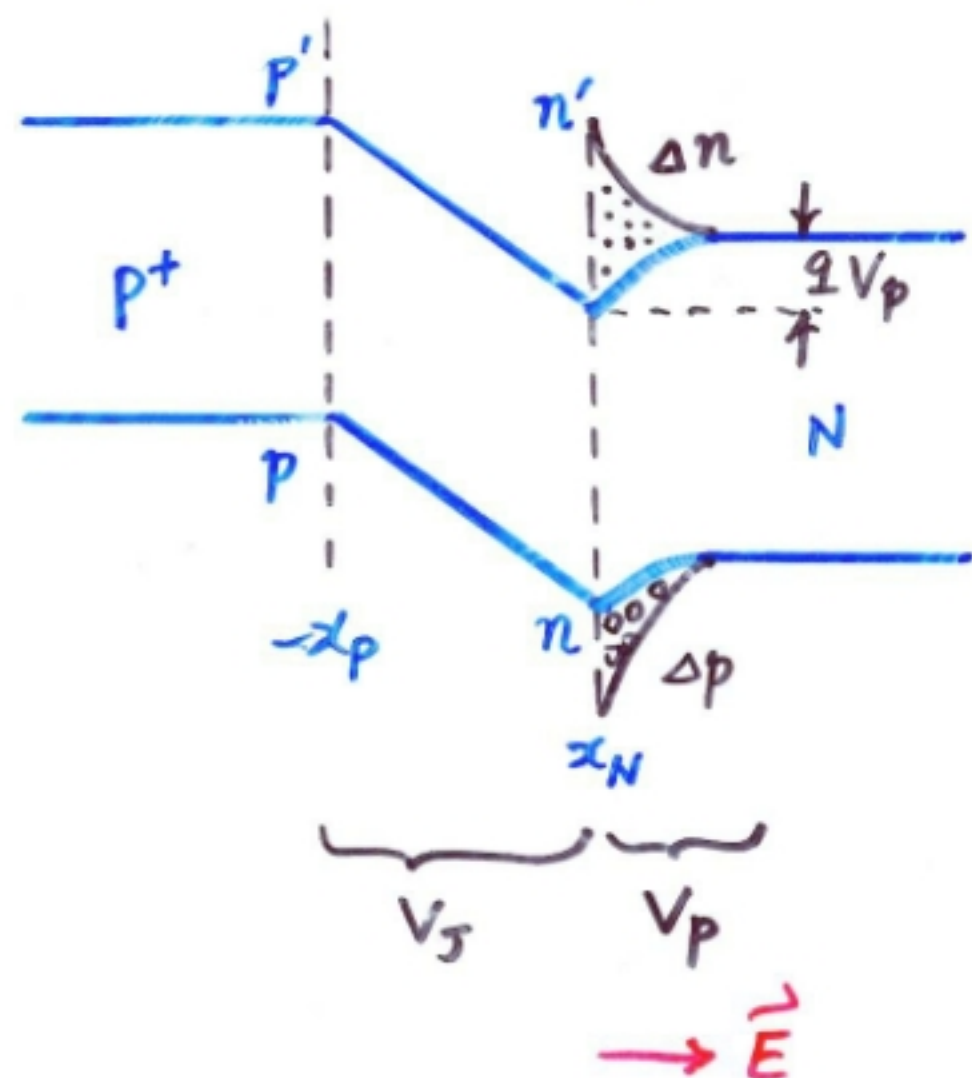
$J_n = q\mu_n n_n(x_n)E(x_n) + qD_n \left. \frac{d\Delta n_n(x)}{dx} \right|_{x=x_n} = 0$

$$E(x_n) = - \frac{D_n}{\mu_n} \frac{1}{n_n(x_n)} \left. \frac{d\Delta n_n(x)}{dx} \right|_{x=x_n}$$

# 8.2 p-n结电流电压特性<sub>17</sub>

## 8.2.5 理想p-n结J-V关系的修正

—大注入条件(正向大偏压)



$$\rightarrow J_p = -qD_p \left[ 1 + \frac{p_n(x_n)}{n_n(x_n)} \right] \frac{d\Delta p_n(x)}{dx} \Big|_{x=x_n}$$

$$D = 2D_p \xleftarrow{\Delta p_n \gg n_{n0}} = -2qD_p \frac{d\Delta p_n(x)}{dx} \Big|_{x=x_n}$$

$$p_n(x_n) = p_{p0} \exp \left[ -\frac{q(V_D - V_J)}{kT} \right] = p_{n0} \exp(qV_J/kT)$$

$$n_n(x_n) = n_{n0} \exp(qV_p/kT)$$

$$p_n(x_n)n_n(x_n) = n_{n0}p_{n0} \exp \left[ \frac{q(V_p + V_J)}{kT} \right] = n_i^2 \exp(qV/kT)$$

$$p_n(x_n) \approx n_n(x_n)$$

$$p_n(x_n) = n_i \exp(qV/2kT)$$



## 8.2 p-n结电流电压特性<sub>17</sub>

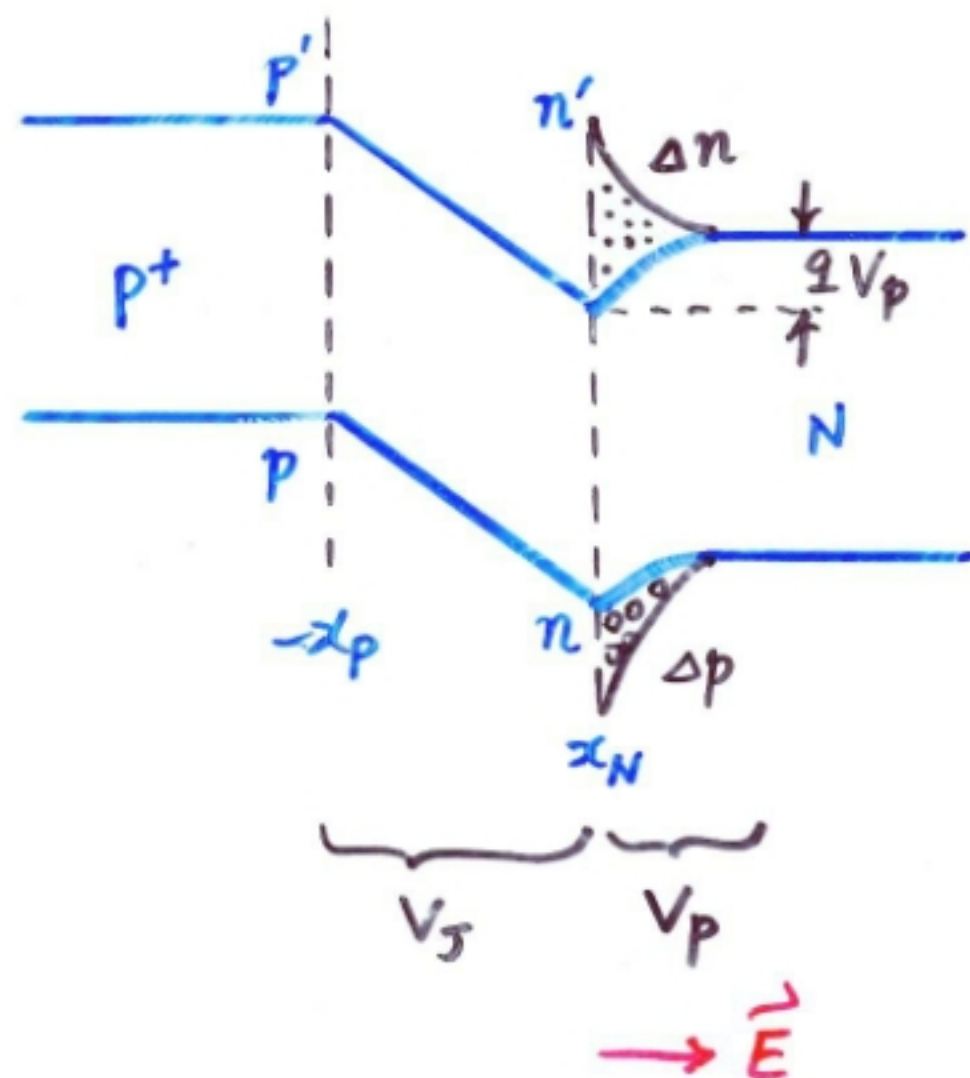
### 8.2.5 理想p-n结J-V关系的修正

—大注入条件(正向大偏压)

$$p_n(x_n) = n_i \exp(qV/2kT) \rightarrow J_p = -2qD_p \left. \frac{d\Delta p_n(x)}{dx} \right|_{x=x_n}$$

线性分布近似

$$\left. \frac{d\Delta p_n(x)}{dx} \right|_{x=x_n} \approx -\frac{p_n(x_n) - p_{n0}}{L_p} \approx -\frac{n_i}{L_p} \exp(qV/2kT)$$



$$J_f = q(2D_p) \frac{n_i}{L_p} \exp(qV/2kT)$$

# 8.2 p-n结电流电压特性<sub>18</sub>

## 8.2.5 理想p-n结J-V关系的修正

— 总结

$$J_r = \frac{qn_i X_D}{2\tau} \exp(qV_f / 2kT)$$

$$J_f = q(2D_p) \frac{n_i}{L_p} \exp(qV / 2kT)$$

